

INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor IPD60R1K4C6,IIPD60R1K4C6

FEATURES

- Static drain-source on-resistance: Ros(on)≤1.4Ω
- Enhancement mode:
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

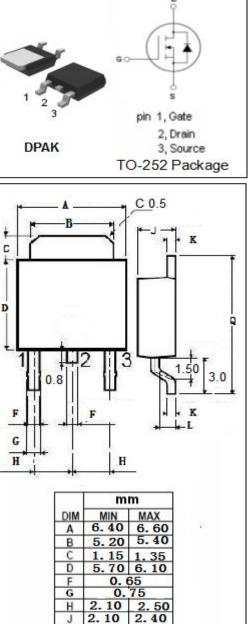
· Fast switching

ADOLLITE MAVIMUM DATINCOT

• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)				
SYMBOL	PARAMETER	VALUE	UNIT	
V _{DSS}	Drain-Source Voltage	600	V	
V_{GS}	Gate-Source Voltage	±20	V	
ID	Drain Current-Continuous	3.2	А	
I _{DM}	Drain Current-Single Pulsed	8	А	
PD	Total Dissipation @T _c =25°C	28.4	W	
Tj	Max. Operating Junction Temperature	150	°C	
T _{stg}	Storage Temperature	-55~150	°C	
	1			

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
Rth(j-c)	Channel-to-case thermal resistance	4.4	°C/W
Rth(j-a)	Rth(j-a) Channel-to-ambient thermal resistance		°C/W



κ

0

0.40

0.90

9.90

0.60

10

10



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ELECTRICAL CHARACTERISTICS

T_c=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =0.25mA	600			V
V _{GS} (th)	Gate Threshold Voltage	VDS=VGS; I _D =0.09mA	2.5		3.5	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =1.1A			1.4	Ω
I _{GSS}	Gate-Source Leakage Current	V _{GS} =20V; V _{DS} =0V			0.1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =600V; V _{GS} = 0V			1	μA
V _{SD}	Diode forward voltage	I _F =1.4A, V _{GS} = 0V		0.9		V

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